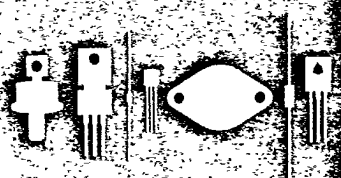


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PN5033

P-CHANNEL JFET

JEDEC TO-92 CASE (DSG)

DESCRIPTION

The CENTRAL SEMICONDUCTOR PN5033 type is a silicon P-channel junction field effect transistor designed for low level amplifier applications.

MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$  unless otherwise noted)

	SYMBOL		UNIT
Drain-Gate Voltage	V <sub>DG</sub>	20	V
Drain-Source Voltage	V <sub>DS</sub>	20	V
Reverse Gate-Source Voltage	V <sub>GSR</sub>	20	V
Gate Current	I <sub>G</sub>	50	mA
Power Dissipation	P <sub>D</sub>	200	mW
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I <sub>GSS</sub>	V <sub>GS</sub> =15V		10	nA
I <sub>GSS</sub>	V <sub>GS</sub> =15V, T <sub>A</sub> =100°C		0.5	μA
I <sub>DSS</sub>	V <sub>DS</sub> =10V	0.3	3.5	mA
BV <sub>GSS</sub>	I <sub>G</sub> =10μA	20		V
V <sub>GS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =0.03mA		2.3	V
V <sub>GS(OFF)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1.0μA	0.3	2.5	V
Y <sub>fs</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0, f=1.0kHz	1000	5000	μmho
Y <sub>os</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0, f=1.0kHz		20	μmho
Re(y <sub>fs</sub> )	V <sub>DS</sub> =10V, V <sub>GS</sub> =0, f=1.0MHz	900		μmho
C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0, f=1.0MHz		25	pF
C <sub>rss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0, f=1.0MHz		7.0	pF
r <sub>ds(ON)</sub>	V <sub>GS</sub> =0, I <sub>D</sub> =0, f=1.0kHz		1300	Ω
NF	V <sub>DS</sub> =10V, V <sub>GS</sub> =0, R <sub>G</sub> =1.0MΩ, f=1.0kHz, BW=150Hz		2.0	dB
eN	V <sub>DS</sub> =10V, V <sub>GS</sub> =0, BW=150Hz		0.1	μV/√Hz

LEAD CODE:

1. DRAIN
2. SOURCE
3. GATE

